

# EVVOSEMI<sup>®</sup>

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

## Product Specification

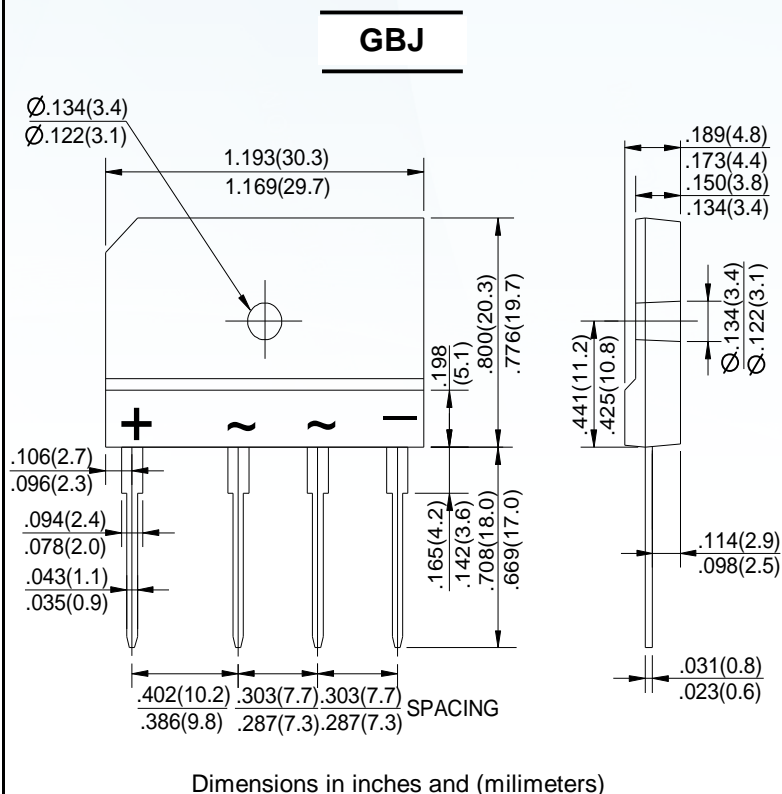
▶ Domestic	Part Number	GBJ15005 - GBJ1510
▶ Overseas	Part Number	GBJ15005 - GBJ1510
▶ Equivalent	Part Number	GBJ15005 - GBJ1510

EV is the abbreviation of name EVVO

**GLASS PASSIVATED  
BRIDGE RECTIFIERS**

 REVERSE VOLTAGE - **50 to 1000Volts**  
 FORWARD CURRENT - **15 Amperes**
**FEATURES**

- Rating to 1000V PRV
- Ideal for printed circuit board
- Low forward voltage drop, high current capability
- Reliable low cost construction utilizing molded plastic technique results in inexpensive product
- The plastic material has UL flammability classification 94V-0


**MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS**

Rating at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%

CHARACTERISTICS	SYMBOL	GBJ 15005	GBJ 1501	GBJ 1502	GBJ 1504	GBJ 1506	GBJ 1508	GBJ 1510	UNIT
Maximum Recurrent Peak Reverse Voltage	V <sub>RRM</sub>	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V <sub>RMS</sub>	30	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V <sub>DC</sub>	50	100	200	400	600	800	1000	V
Maximum Average Forward (with heatsink Note 2) Rectified Current @ T <sub>C</sub> =100°C (without heatsink)	I <sub(av)< sub=""></sub(av)<>	15.0 3.2							A
Peak Forward Surge Current 8.3ms Single Half Sine-Wave Super Imposed on Rated Load (JEDEC Method)	I <sub>FSM</sub>	240							A
Maximum Forward Voltage at 7.5A DC	V <sub>F</sub>	1.1							V
Maximum DC Reverse Current @ T <sub>J</sub> =25°C at Rated DC Blocking Voltage @ T <sub>J</sub> =125°C	I <sub>R</sub>	10.0 500							uA
I <sup>2</sup> t Rating for Fusing (t<8.3ms)	I <sup>2</sup> t	240							A <sup>2</sup> s
Typical Junction Capacitance Per Element (Note1)	C <sub>J</sub>	60							pF
Typical Thermal Resistance (Note2)	R <sub>θJC</sub>	0.8							°C/W
Operating Temperature Range	T <sub>J</sub>	-55 to +150							°C
Storage Temperature Range	T <sub>STG</sub>	-55 to +150							°C

NOTES: 1. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

2. Device mounted on 300mm\*300mm\*1.6mm cu plate heatsink.

FIG.1-FORWARD CURRENT DERATING CURVE

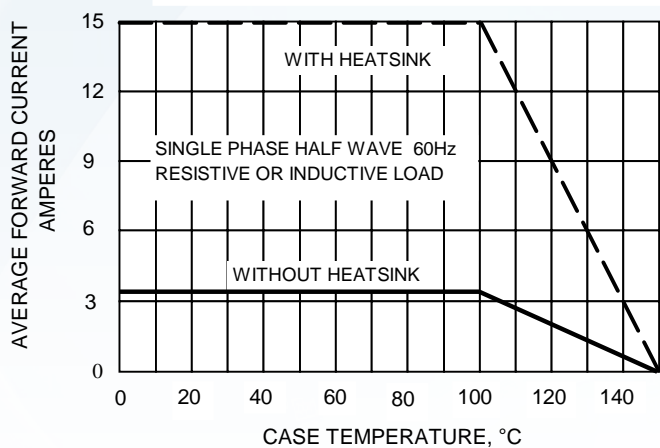


FIG.2-MAXMUN NON-REPETITIVE SURGE CURRENT

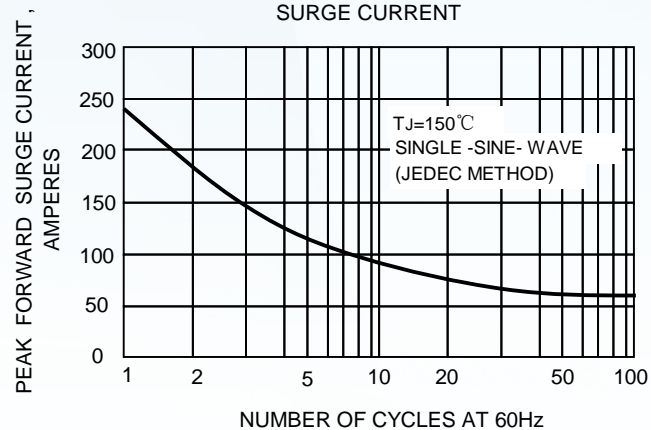


FIG.3-TYPICAL JUNCTION CAPACITANCE

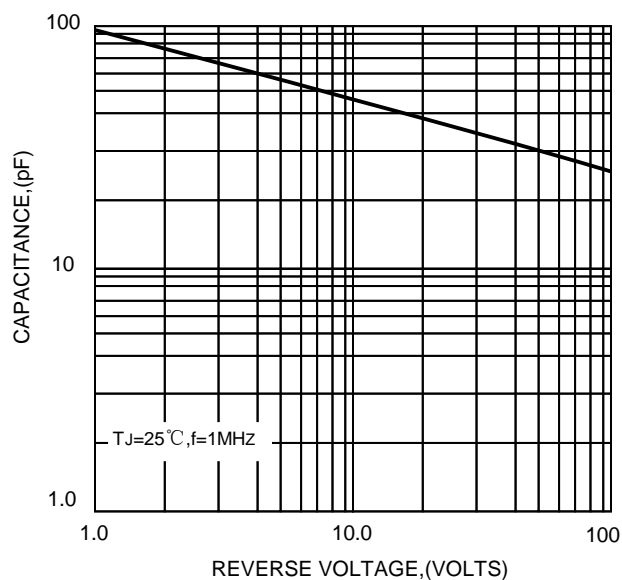


FIG.4-TYPICAL FORWARD CHARACTERISTICS

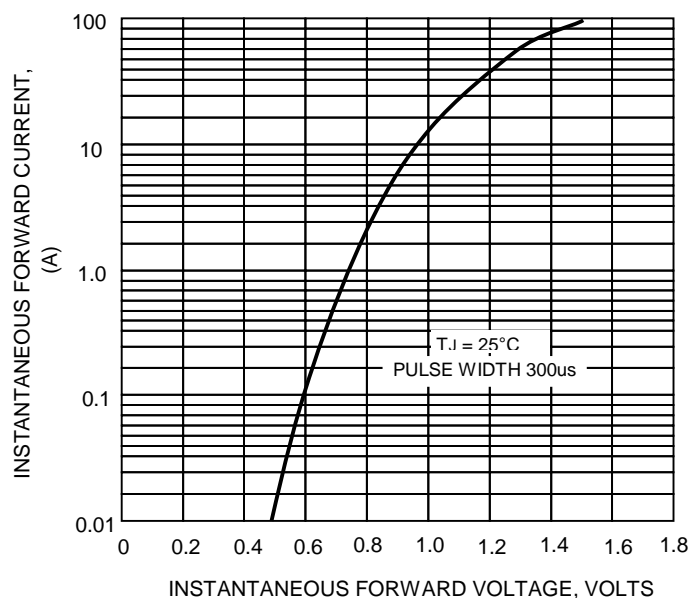
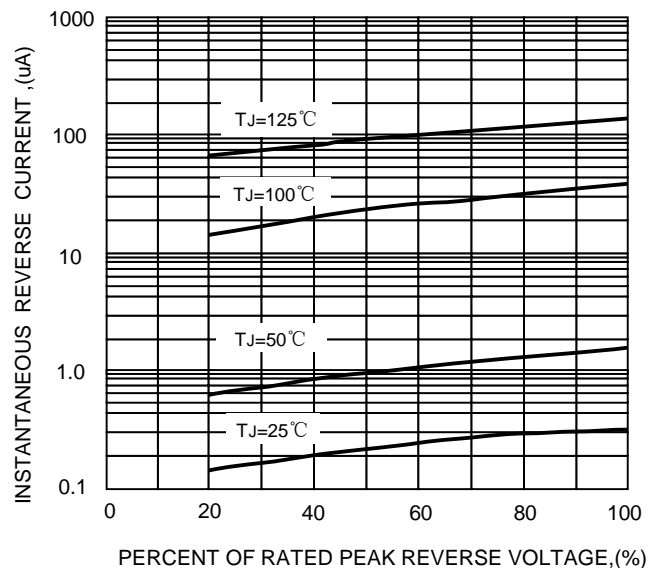


FIG.5-TYPICAL REVERSE CHARACTERISTICS



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